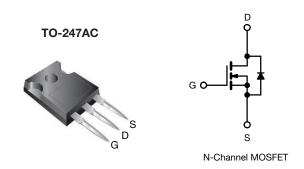
Vishay Siliconix

COMPLIANT

HALOGEN

FREE

E Series Power MOSFET



PRODUCT SUMMARY				
V _{DS} (V) at T _J max.	65	0		
R _{DS(on)} typ. (Ω) at 25 °C	V _{GS} = 10 V 0.137			
Q _g max. (nC)	36			
Q _{gs} (nC)	10			
Q _{gd} (nC)	6			
Configuration	Single			

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) Ron x Qg
- Low effective capacitance (Co(er))
- · Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

ORDERING INFORMATION	
Package	TO-247AC
Lead (Pb)-free and halogen-free	SiHG150N60E-GE3

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	600	V
Gate-source voltage			V_{GS}	± 30	v
Continuous drain surrent (T. 150 °C)	V et 10 V	$T_{\rm C} = 25 ^{\circ}{\rm C}$ $T_{\rm C} = 100 ^{\circ}{\rm C}$		22	
Continuous drain current (T _J = 150 °C) $V_{GS} \text{ at 10 V} \frac{T_C = 23 \text{ C}}{T_C = 100 \text{ °C}}$		T _C = 100 °C	· I _D	14	Α
Pulsed drain current ^a			I _{DM}	43	
Linear derating factor				1.42	W/°C
Single pulse avalanche energy b			E _{AS}	111	mJ
Maximum power dissipation			P_{D}	179	W
Operating junction and storage temperature range			T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope $T_J = 125 ^{\circ}\text{C}$		dv/dt	100	V/ns	
Reverse diode dv/dt ^d			av/at	5	V/ns
Soldering recommendations (peak temperatur	e) ^c	For 10 s		260	°C

- a. Repetitive rating; pulse width limited by maximum junction temperature
- b. V_{DD} = 120 V, starting T_J = 25 °C, L = 28.2 mH, R_q = 25 Ω , I_{AS} = 2.8 A
- c. 1.6 mm from case
- d. $I_{SD} \le I_D$, di/dt = 100 A/ μ s, starting $T_J = 25$ °C



Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R _{thJA}	=	40	°C/W
Maximum junction-to-case (drain)	R _{thJC}	-	0.7	C/VV

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				L			
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		600	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I _D = 1 mA	-	0.62	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = 250 μA	3.0	-	5.0	V
Cata aguraa laakaga		,	$V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
Gate-source leakage	I _{GSS}	,	$V_{GS} = \pm 30 \text{ V}$	-	-	± 1	μΑ
Zava cata valtaca dvain august	1	V _{DS} =	600 V, V _{GS} = 0 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 480 V	, V _{GS} = 0 V, T _J = 125 °C	-	-	10	μA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.137	0.158	Ω
Forward transconductance	9 _{fs}	V _{DS}	= 10 V, I _D = 10 A	-	5.1	-	S
Dynamic							
Input capacitance	C _{iss}		V _{GS} = 0 V,	-	1514	-	
Output capacitance	C _{oss}		$V_{DS} = 100 \text{ V},$	-	60	-	1
Reverse transfer capacitance	C _{rss}	f = 100 KHz		-	2	-	
Effective output capacitance, energy related	C _{o(er)}	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		-	58	-	pF
Effective output capacitance, time related	C _{o(tr)}			-	322	-	
Total gate charge	Qg			-	24	36	
Gate-source charge	Q_{gs}	$V_{GS} = 10 \text{ V}$	$V_{GS} = 10 \text{ V}$ $I_{D} = 10 \text{ A}, V_{DS} = 480 \text{ V}$		10	-	nC
Gate-drain charge	Q_gd			-	6	-	
Turn-on delay time	t _{d(on)}			-	20	40	
Rise time	t _r	V _{DD} =	$V_{DD} = 480 \text{ V}, I_D = 10 \text{ A},$		27	54	no
Turn-off delay time	t _{d(off)}	V _{GS} =	$=$ 10 V, R _g = 9.1 Ω	-	28	56	ns
Fall time	t _f			-	17	34	
Gate input resistance	R_g	f = 1	MHz, open drain	0.4	0.9	1.8	Ω
Drain-Source Body Diode Characteristic	es						
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	22	
Pulsed diode forward current	I _{SM}			-	-	43	A
Diode forward voltage	V _{SD}	T _J = 25 °C	C, I _S = 10 A, V _{GS} = 0 V	-	-	1.2	V
Reverse recovery time	t _{rr}			-	291	582	ns
Reverse recovery charge	Q _{rr}		$5 ^{\circ}\text{C}, I_{\text{F}} = I_{\text{S}} = 10 \text{A},$	-	3.5	7.0	μC
Reverse recovery current	I _{RRM}	di/dt = 100 A/μs, V _R = 25 V		_	21	-	Α



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

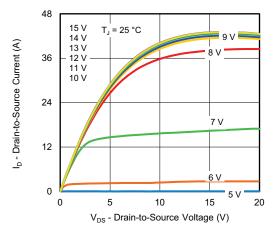


Fig. 1 - Typical Output Characteristics

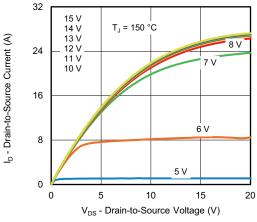


Fig. 2 - Typical Output Characteristics

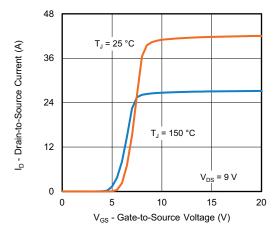


Fig. 3 - Typical Transfer Characteristics

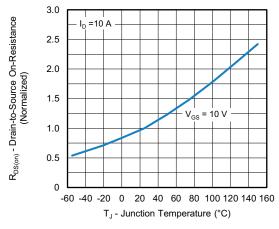


Fig. 4 - Normalized On-Resistance vs. Temperature

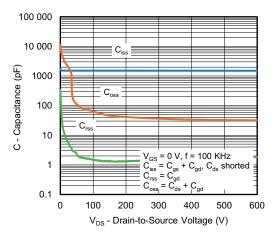


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

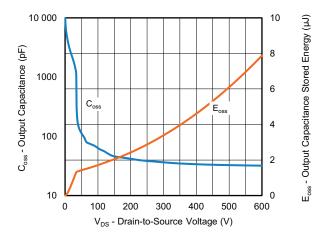


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}



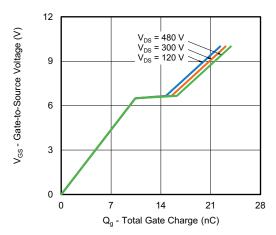


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

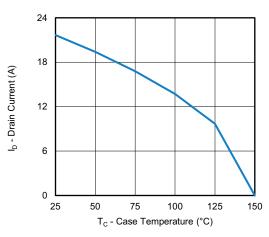


Fig. 9 - Maximum Drain Current vs. Case Temperature

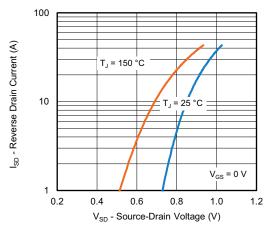


Fig. 8 - Typical Source-Drain Diode Forward Voltage

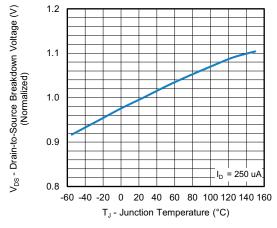


Fig. 10 - Temperature vs. Drain-to-Source Voltage

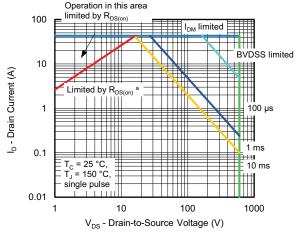


Fig. 11 - Maximum Safe Operating Area

Note

a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



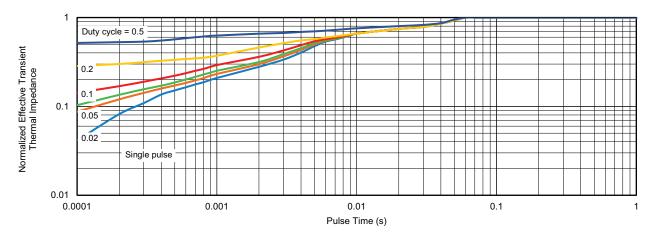


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

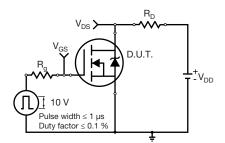


Fig. 13 - Switching Time Test Circuit

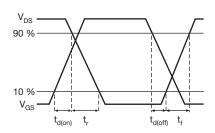


Fig. 14 - Switching Time Waveforms

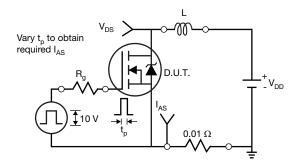


Fig. 15 - Unclamped Inductive Test Circuit

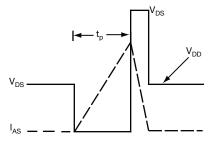


Fig. 16 - Unclamped Inductive Waveforms

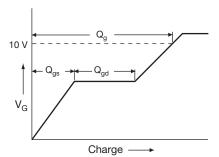


Fig. 17 - Basic Gate Charge Waveform

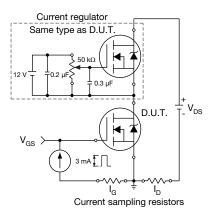
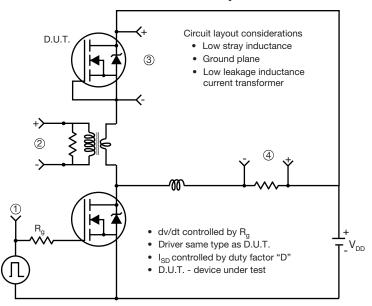


Fig. 18 - Gate Charge Test Circuit



Peak Diode Recovery dv/dt Test Circuit



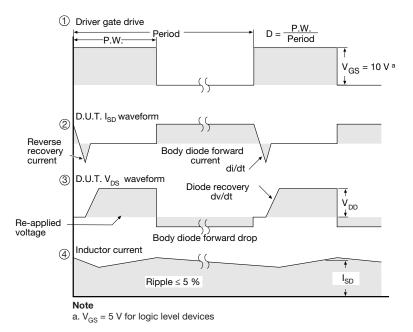


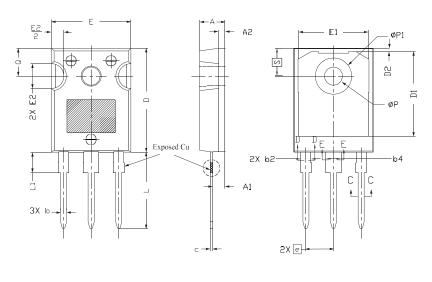
Fig. 19 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?92450.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D-D,E-E

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTES	
Α	4.83	5.02	5.21		
A1	2.29	2.41	2.55		
A2	1.17	1.27	1.37		
b	1.12	1.20	1.33		
b1	1.12	1.20	1.28		
b2	1.91	2.00	2.39	6	
b3	1.91	2.00	2.34		
b4	2.87	3.00	3.22	6, 8	
b5	2.87	3.00	3.18		
С	0.40	0.50	0.60	6	
c1	0.40	0.50	0.56		
D	20.40	20.55	20.70	4	

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
Е	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

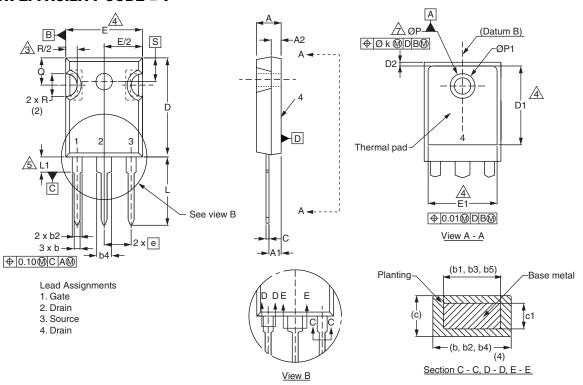
- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



www.vishay.com

Vishay Siliconix

VERSION 2: FACILITY CODE = Y



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

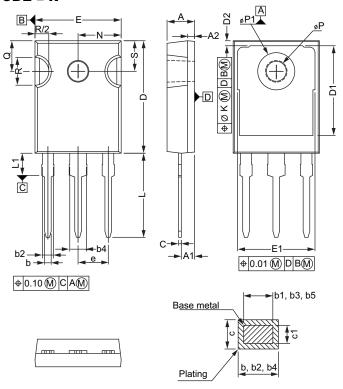
	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	0.254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

www.vishay.com

Vishay Siliconix

VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.